

REMARKS

Applicants will address each of the Examiner's objections and rejections in the order in which they appear in the Office Action.

Claim Objections

The Examiner objects to informalities in Claims 28 and 34. Applicants have amended each of these claims as suggested by the Examiner to correct the typo in each.

Claim Rejections - 35 USC §102

Claims 40, 44 and 45 rejected over Yamazaki '818

The Examiner also rejects Claims 40, 44 and 45 under 35 U.S.C. §102 as being anticipated by Yamazaki et al. '818. This rejection is respectfully traversed.

Independent Claim 40 requires a second wiring formed on a first wiring. The Examiner alleges that this is shown in Figs. 2C and 8A-8B of Yamazaki '818 wherein the first wiring layer is reference numerals 146-150 and the second wiring layer is reference numerals 152-155.

However, Fig. 2C, for example, of Yamazaki '818 does not show layers 152-155 formed on layers 146-150. In fact, they do not appear to be contact with each other. Hence, Yamazaki '818 cannot anticipate nor render obvious independent Claim 40 or dependent Claims 44 and 45. Accordingly, it is requested that this rejection be withdrawn.

Claims 40 and 44 rejected over Zhang '701

The Examiner also rejects Claims 40 and 44 under 35 U.S.C. §102 as being anticipated by Zhang '701. This rejection is also respectfully traversed.

As stated supra, independent Claim 40 requires a second wiring formed on a first wiring. The Examiner alleges that this is shown in Fig. 1 of Zhang '701 wherein the first wiring layer is reference numeral 113 and the second wiring layer is reference numeral 115.

However, Fig. 1 of Zhang '701 does not show layer 115 formed on layer 113. In fact, they do not appear to be contact with each other. Hence, Zhang '701 cannot anticipate nor render obvious independent Claim 40 or dependent Claim 44. Accordingly, it is requested that this rejection be withdrawn.

Claim Rejections - 35 USC §103

Claims 1-12, 19-24, 28-33, 41-43 and 45 rejected over Zhang '701 and Yamazaki '542

The Examiner also rejects Claims 1-12, 19-24, 28-33, 41-43 and 45 under 35 U.S.C. §103: as being unpatentable over Zhang '701 in view of Yamazaki '542. This rejection is also respectfully traversed.

Each of these claims requires either:

(a) a second metallic layer formed on a first metallic layer and the second metallic layer directly connected to a conductive layer (Claim 1-6);

(b) a second metallic layer formed on a first metallic layer and the second conductive layer directly connected to a source or drain region of a thin film transistor (Claim 7-12);

(c) a second conductive layer formed on a first conductive layer and the second conductive layer directly connected to a source or drain region (Claim 19-24);

(d) a second conductive layer formed on a first conductive layer and the second conductive layer directly connected to a semiconductor layer of a TFT (Claim 28-33).

The Examiner alleges that Zhang '701 discloses all of these limitations (Yamazaki '542 being cited for another limitation). However, as explained above, Zhang '701 does not disclose or suggest a second metallic or conductive layer formed on a first metallic or conductive layer. The alleged layers in Zhang '701 are not even in contact with each other. Further, layer 115 in Zhang '701 is in contact with an insulating layer 109, not directly connected to a source or drain region or a conductive or semiconductor layer, as required in the rejected claims.

Hence, Zhang '701 and Yamazaki '542 do not render obvious the rejected claims. Accordingly, it is requested that this rejection be withdrawn.

Claims 1-12, 19-24 and 28-45 rejected over Yano et al. '429 and Yamazaki '542.

The Examiner also rejects Claims 1-12, 19-24 and 28-45 under 35 U.S.C. §103 as being unpatentable over Yano et al. '429 in view of Yamazaki '542. This rejection is also respectfully traversed.

Each of the rejected claims requires a pixel electrode formed on a second insulating film. The Examiner alleges that reference numeral 43B in Yano '429 is a pixel electrode. However, the reference describes 43B as a "third-layer metal wiring". There is no mention in the reference of a pixel electrode. Accordingly, it is requested that this rejection be withdrawn.

Claims 1-12, 19-24, 28-33 and 41-43 rejected over Yamazaki et al. '818

Finally, the Examiner rejects Claims 1-12, 19-24, 28-33 and 41-43 under 35 U.S.C. §103 as being unpatentable over Yamazaki et al. '818. This rejection is also respectfully traversed.

Each of these claims requires either:

(a) a second metallic layer formed on a first metallic layer and the second metallic layer directly connected to a conductive layer (Claim 1-6);

(b) a second metallic layer formed on a first metallic layer and the second conductive layer directly connected to a source or drain region of a thin film transistor (Claim 7-12);

(c) a second conductive layer formed on a first conductive layer and the second conductive layer directly connected to a source or drain region (Claim 19-24);

(d) a second conductive layer formed on a first conductive layer and the second conductive layer directly connected to a semiconductor layer of a TFT (Claim 28-33).

The Examiner alleges that Yamazaki '818 discloses all of these limitations. However, as explained above, Yamazaki '818 does not disclose or suggest a second metallic or conductive layer formed on a first metallic or conductive layer. The alleged layers in Yamazaki '818 are not even in contact with each other.

Hence, Yamazaki '818 does not render obvious the rejected claims. Accordingly, it is requested that this rejection be withdrawn.

Conclusion

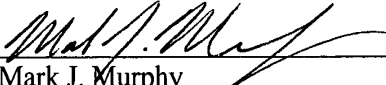
It is respectfully submitted that the present application is now in a condition for allowance.

Applicants do not believe that any further fee is due for this amendment. Please charge our Deposit Account No. 50-1039 for any deficiency.

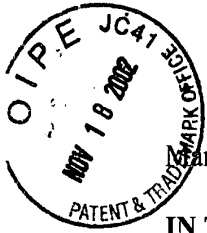
Favorable reconsideration is earnestly solicited.

Respectfully submitted,

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Marked up copy of the claims as amended:

IN THE CLAIMS:

Please amend the claims as follows:

28. (Third Amendment) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer through a contact hole provided in said second insulating film, wherein said second conductive layer is directly connected to said semiconductor layer [though] through a contact hole provided in said first insulating film.

34. (Third Amendment) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

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a second insulating film formed on said second conductive layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer through a contact hole provided in said second insulating film,

wherein said second conductive layer is directly connected to said semiconductor layer [though] through a contact hole provided in said first conductive layer and said first insulating film.